AlGaAs/AlGaAs Epitaxial Wafer for IR LED

	MODEL NUMBER		LGP8302-25-DDH				LGP8502-25-DDH				LGP8602-25-DDH				LGP8900-25-DDH			
STRUCTURE & MATERIAL SPECIFICATION	ITEM	UNIT	3rd layer	2nd layer	1st layer	substrate **(removed)**	3rd layer	2nd layer	1st layer	substrate **(removed)**	3rd layer	2nd layer	1st layer	substrate **(removed)**	3rd layer	2nd layer	1st layer	substrate **(removed)**
	Material		AlGaAs	AlGaAs	AlGaAs	GaAs	AlGaAs	AlGaAs	AlGaAs	GaAs	AlGaAs	AlGaAs	AlGaAs	GaAs	AlGaAs	GaAs	AlGaAs	GaAs
	Growth Method		Liquid Phase Epitaxy			HB/VGF	Liquid Phase Epitaxy			HB/VGF	Liquid Phase Epitaxy			HB/VGF	Liquid Phase Epitaxy			HB/VGF
	Conduction Type		P	P	N	N	P	P	N	N	P	P	N	N	P	P	N	N
	Carrier Conc.	cm^{-3}	$1.0x10^{18}$ Min.		$2.0x10^{17}$ Min.	$2~20x10^{17}$	$1.0x10^{18}$ Min.		$2.0x10^{17}$ Min.	$2~20x10^{17}$	$1.0x10^{18}$ Min.		$2.0x10^{17}$ Min.	$2~20x10^{17}$	$1.0x10^{18}$ Min.		$2.0x10^{17}$ Min.	$2~20x10^{17}$
	Thickness	um	10~40	1.0 Typ.	110~220		10~40	1.0 Typ.	110~220		10~40	1.0 Typ.	110~220		10~40	1.0 Typ.	110~220	
	E.P.D	cm^{-2}				$1x10^4$ Max.				$1x10^4$ Max.				$1x10^4$ Max.				$1x10^4$ Max.
	Orientation					(100)±0.5deg.				(100)±0.5deg.				(100)±0.5deg.				(100)±0.5deg.
CHARACTERISTICS	E.L. Wavelength (at IF=20mA)	nm	830±10				850±10				860±10				890±10			
	Output Power (at IF=20mA)	mV	5.0 Min. (PROWTech Unit)				5.0 Min. (PROWTech Unit)				5.0 Min. (PROWTech Unit)				5.0 Min. (PROWTech Unit)			
	Surface/Backside Appearance		As Grown/Etching				As Grown/Etching				As Grown/Etching				As Grown/Etching			
	Total Thickness	um	120~220				120~220				120~220				120~220			
	Diameter	mm	61 Max				61 Max				61 Max				61 Max			

Notes

1. These models are suitable for use as the light source in a wide range of optical control.
2. These specifications are subject to change without notice.

32, GWAHAKSANEOP 3-RO, OKSAN-MYEON, CHEONGWON-GUN, CHUNGCHEONGBUK-DO, (363-911) KOREA